

FAST - [10506752.wsp1]

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S154: (1) (mesa valley) with (memory near array near structure)

S155: (0) msilicon adj mesa

S156: (519) silicon adj mesa

S157: (1975) silicon adj valley

S158: (5) S156 and S157

S159: (0) 2005/0212033

S160: (2) "20050212033"

S161: (497) mesa near (transistor source drain)

S162: (444) S161 and (@ad<"20040811" @rlad<"20040811")

S163: (0) (mesa near (transistor source drain)) and (valley near

S164: (497) (mesa near (transistor source drain)) and (transistor

S165: (444) S164 and (@ad<"20040811" @rlad<"20040811")

S166: (497) (mesa near (transistor source drain))

S167: (444) S166 and (@ad<"20040811" @rlad<"20040811")

S168: (5136) heterojunction adj bipolar adj transistor

S169: (50) S168 and (mesa near transistor)

S170: (50) S169 and (@ad<"20040811" @rlad<"20040811")

S171: (1) 2002/0008988

S172: (1) "20020008988".FN.

S173: (602) (magnetic near memory near array)

S174: (21) S173 with shieldS3

S175: (18) S174 and (@ad<"20030115" @rlad<"20030115")

S176: (18) (pinned near layer) same (changeable near layer)

S177: (23) (pinned near layer) and (changeable near layer)

S178: (6) S177 and shieldS3

Search List Browse Query Clear

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Default operator: OR

S178 and (@ad<"20030115" @rlad<"20030115")

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	U	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	2	3	4	5
1	<input type="checkbox"/>	US 20020135935 A1	20020926	18	Write head with magnetization controlled by	360/126			Covington, Mark William	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 6809900 B2	20041026	18	Write head with magnetization controlled by	360/126			Covington, Mark William	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 6635499 B1	20031021	8	MRAM sense layer isolation	438/3	257/E21.665; 257/E27.005		Signorini, Karen	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 6485989 B1	20021126	8	MRAM sense layer isolation	438/3	257/295; 257/E21.665;		Signorini, Karen	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 6385082 B1	20020507	10	Thermally-assisted magnetic random access memory (MRAM)	365/171	365/145; 365/158;		Abraham, David W. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Hit: Details HTML

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